



- ☐ Drafts
- ☐ Pending
- ☒ Active
 - L1: (259) memory and substrate and trench and memory near cell\$1 and trench near line
 - L2: (187) memory and substrate and trench and memory near cell\$1 and trench near line and gate an...
 - L3: (59) memory near flash and substrate and trench and memory near cell\$1 and trench near line a...
 - L4: (4) memory near flash and substrate and trench and memory near cell\$1 and trench adj line and...
 - L5: (16) memory and substrate and trench and memory near cell\$1 and trench adj line and gate and...
 - L6: (6) memory near flash and substrate and trench adj line
 - L7: (13) (first adj2 column) with trench
- ☐ Failed
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- ☐ UDC
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DBs US-PGPUB: USPAT: USI Plurals

Default operator: OR ☒ Highlight all hit terms initially

(first adj2 column) with trench

BRS form IS&R form Image Text HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20050123257 A1	20050609	11	Optical fiber of complex index profile	385/127	
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20050017283 A1	20050127		Semiconductor device	257/301	
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20030180020 A1	20030925		Optical fiber of complex index profile	385/127	
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20030169629 A1	20030911		Semiconductor memory cell configuration and a method for producing the configuration	365/200	257/E21.652
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20030096429 A1	20030522		Laser-induced cell lysis system	436/174	422/99; 436/63
6	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6904216 B2	20050607		Optical fiber of complex index profile	385/127	
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6853023 B2	20050208		Semiconductor memory cell configuration and a method for producing the configuration	257/301	257/302; 257/774; 257/E21.652
8	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6815209 B2	20041109		Laser-induced cell lysis system	436/63	422/99; 435/287.1; 435/290
9	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6566691 B1	20030520		Semiconductor device with trench gate having structure to promote conductivity modulation	257/139	257/133; 257/330; 257/E21.384
10	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5529944 A	19960625		Method of making cross point four square folded bitline trench DRAM cell	438/242	257/E21.652; 257/E27.096; 438/246
11	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5173436 A	19921222		Method of manufacturing an EEPROM with trench-isolated bitlines	438/262	257/E21.209; 257/E21.552; 257/E21.68

eDAN 1.6.1 - ... EAST - [107... EAST Brows... EAST Brows... Document3 - ... Inbox - Micro...